



YEA SHIN TECHNOLOGY CO., LTD

YSE2319WKL

P-Channel Enhancement MOSFET

V_{DS}= -20V, ID= -0.25A



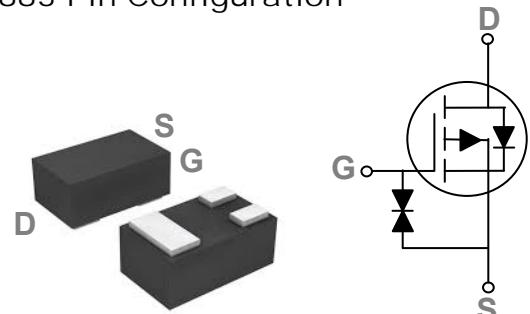
Features

- -20V,-250mA, $R_{DS(ON)} = 650m\Omega$ @ $V_{GS} = -4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- Suit for -1.5V Gate Drive Applications

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

SOT-883 Pin Configuration



Absolute Maximum Rating $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 8	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	-250	mA
	Drain Current – Continuous ($T_c=100^\circ C$)	-160	mA
I_{DM}	Drain Current – Pulsed ¹	-1	A
P_D	Power Dissipation ($T_c=25^\circ C$)	1.55	mW
	Power Dissipation – Derate above $25^\circ C$	1.25	$mW/^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	800	$^\circ C/W$

DEVICE CHARACTERISTICS

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{D}}=-250\mu\text{A}$	-20	---	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $\text{I}_{\text{D}}=-1\text{mA}$	---	-0.01	---	$^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=-20\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{T}_J=25^\circ\text{C}$	---	---	-1	μA
		$\text{V}_{\text{DS}}=-16\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{T}_J=125^\circ\text{C}$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 8\text{V}, \text{V}_{\text{DS}}=0\text{V}$	---	---	± 20	μA

On Characteristics

$\text{R}_{\text{DS(ON)}}$	Static Drain-source On-Resistance	$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_{\text{D}}=-4\text{A}$	---	500	650	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-2.5\text{V}, \text{I}_{\text{D}}=-3\text{A}$	---	700	900	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-1.8\text{V}, \text{I}_{\text{D}}=-3\text{A}$	---	1100	1400	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-1.5\text{V}, \text{I}_{\text{D}}=-3\text{A}$	---	1700	2300	$\text{m}\Omega$
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}, \text{I}_{\text{D}}=-250\mu\text{A}$	-0.3	-0.7	-1	V
$\Delta \text{V}_{\text{GS(th)}}$	$\text{V}_{\text{GS(th)}}$ Temperature Coefficient		---	3	---	$\text{mV}/^\circ\text{C}$

Dynamic and Switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$\text{V}_{\text{DS}}=-10\text{V}, \text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_{\text{D}}=-0.2\text{A}$	---	1	2	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	0.28	0.5	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	0.18	0.4	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time ^{2,3}	$\text{V}_{\text{DD}}=-10\text{V}, \text{V}_{\text{GS}}=-4.5\text{V}, \text{R}_G=10\Omega, \text{I}_{\text{D}}=-0.2\text{A}$	---	8	16	ns
T_r	Rise Time ^{2,3}		---	5.2	10	
$\text{T}_{\text{d(off)}}$	Turn-On Delay Time ^{2,3}		---	30	60	
T_f	Fall Time ^{2,3}		---	18	36	
C_{iss}	Input Capacitance	$\text{V}_{\text{DS}}=-10\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{f}=1\text{MHz}$	---	40	78	pF
C_{oss}	Output Capacitance		---	15	30	
C_{rss}	Reverse Transfer Capacitance		---	6.5	13	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current	$\text{V}_{\text{G}}=\text{V}_{\text{D}}=0\text{V}$, Force Current	---	---	-0.25	A
I_{SM}	Pulsed Source Current		---	---	-0.5	A
V_{SD}	Diode Forward Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{S}}=-0.2\text{A}, \text{T}_J=25^\circ\text{C}$	---	---	-1	V

Note :

- Repetitive Rating : Pulsed width limited by maximum junction temperature.
- The data tested by pulsed , pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.
- Essentially independent of operating temperature.

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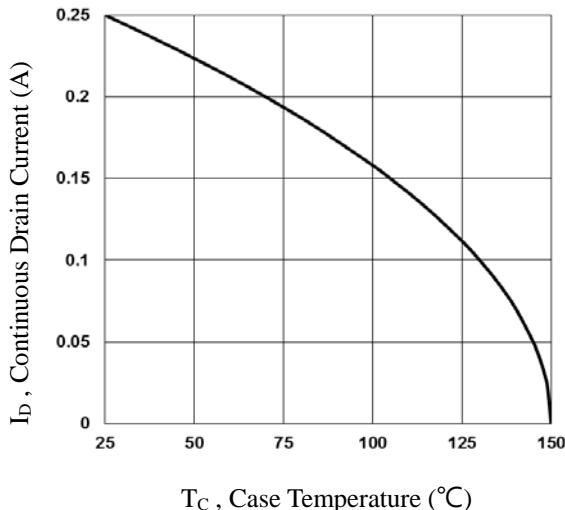


Fig.1 Continuous Drain Current vs. T_c

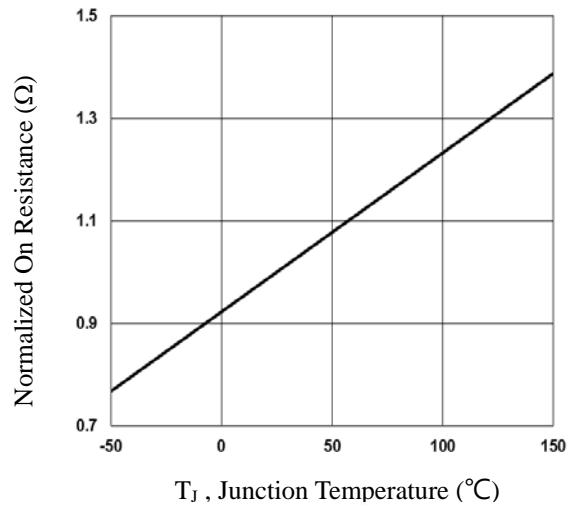


Fig.2 Normalized RDSON vs. T_j

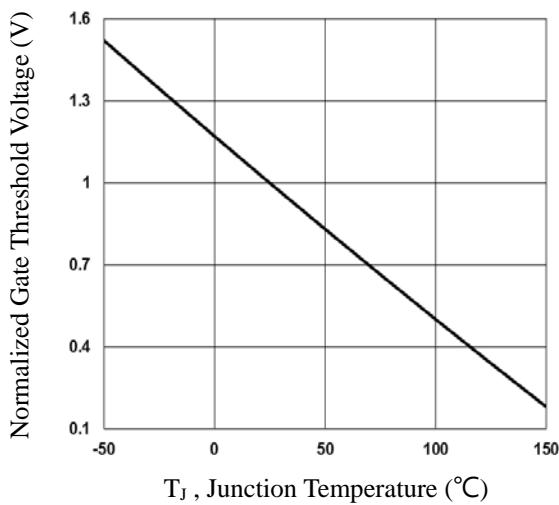


Fig.3 Normalized V_{th} vs. T_j

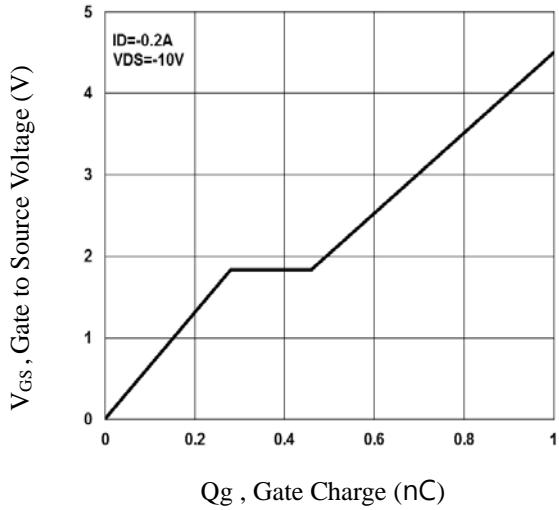


Fig.4 Gate Charge Waveform

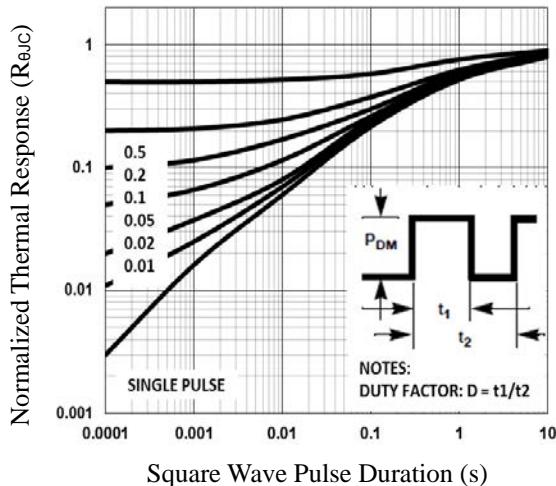


Fig.5 Normalized Transient Impedance

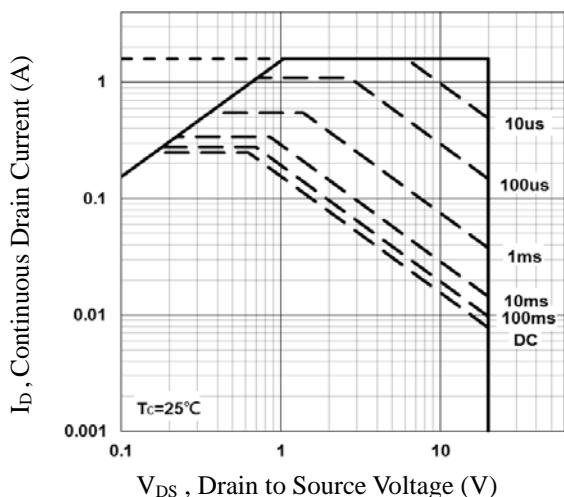


Fig.6 Maximum Safe Operation Area

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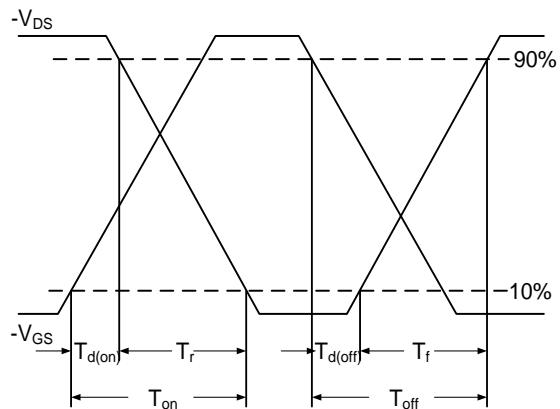


Fig.7 Switching Time Waveform

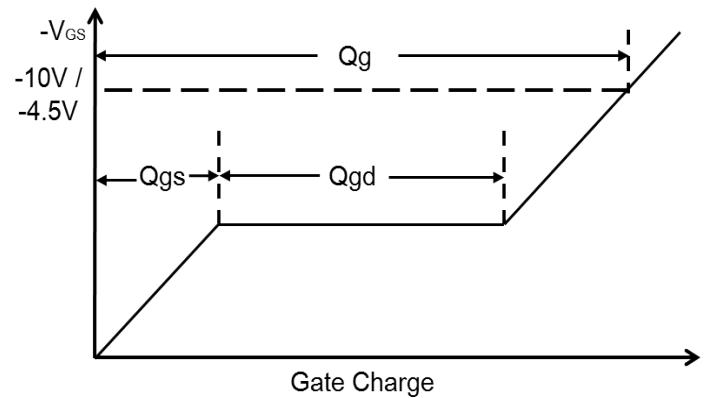
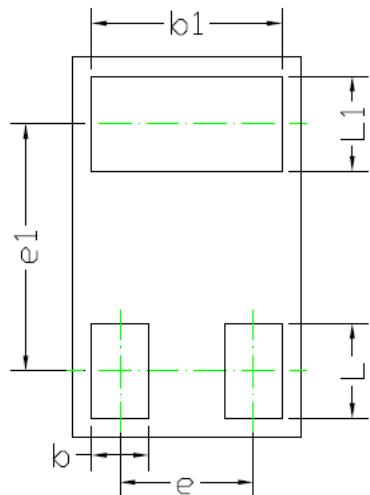
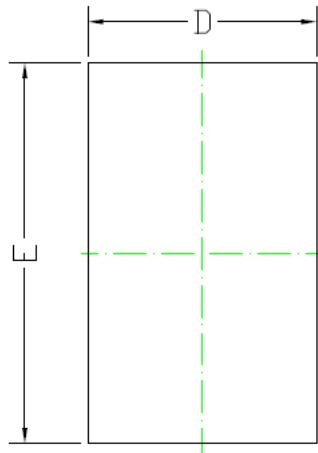


Fig.8 Gate Charge Waveform

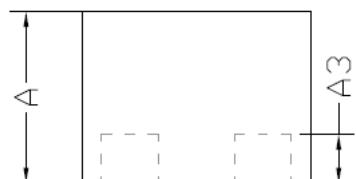
PACKAGE OUTLINE & DIMENSIONS

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SOT-883 PACKAGE INFORMATION



SIDE VIEW



SYMBOL	COMMON		
	DIMENSIONS MILLIMETER		
	MIN	NOM.	MAX
A	0.40	0.45	0.50
A3	0.127 BSC		
D	0.55	0.60	0.65
E	0.95	1.00	1.05
e	0.35 BSC		
e1	0.65 BSC		
b	0.13	0.15	0.18
b1	0.45	0.50	0.55
L	0.20	0.25	0.30
L1	0.20	0.25	0.30